



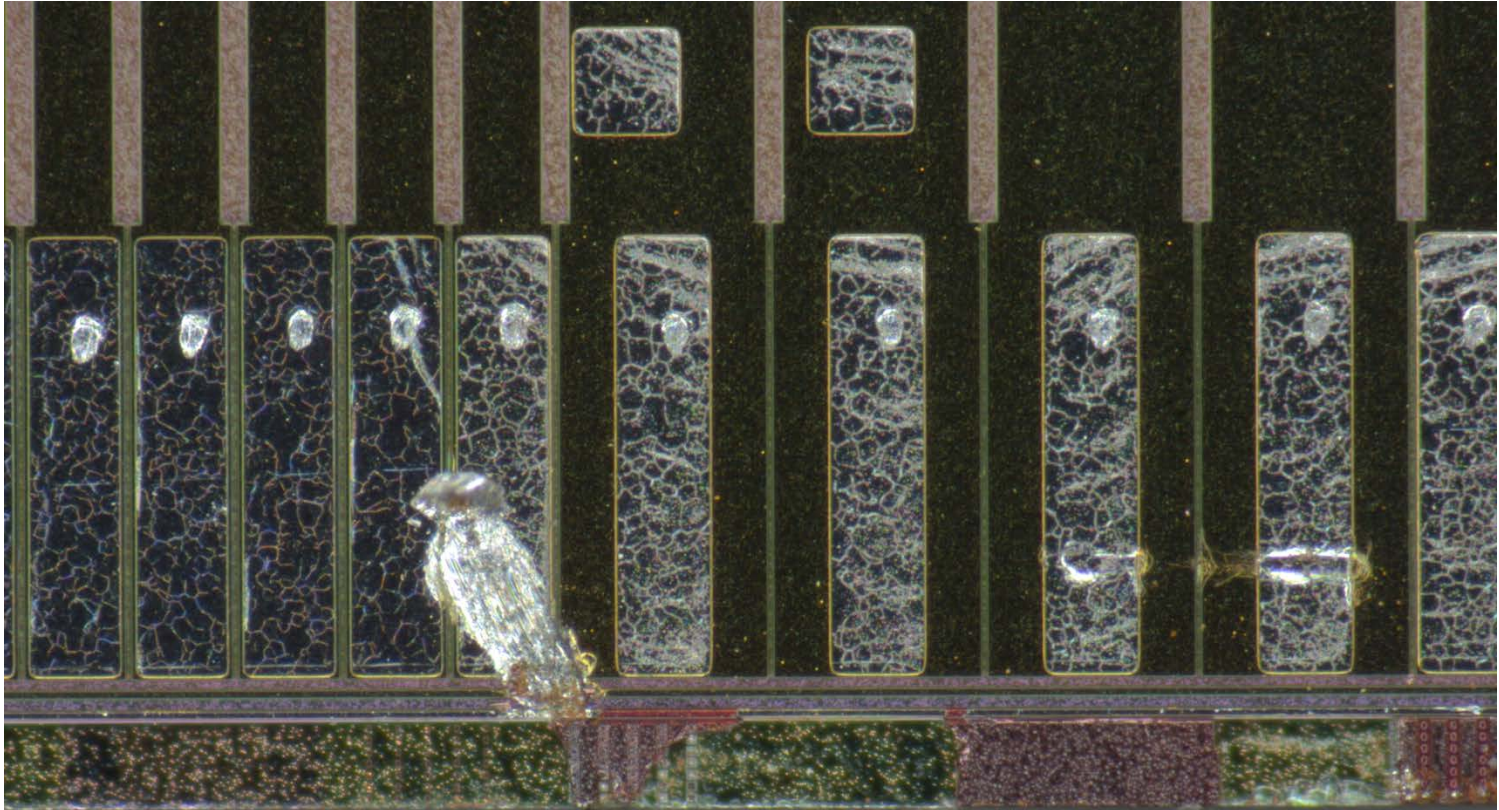
## InGrid issues

Fred Hartjes  
NIKHEF

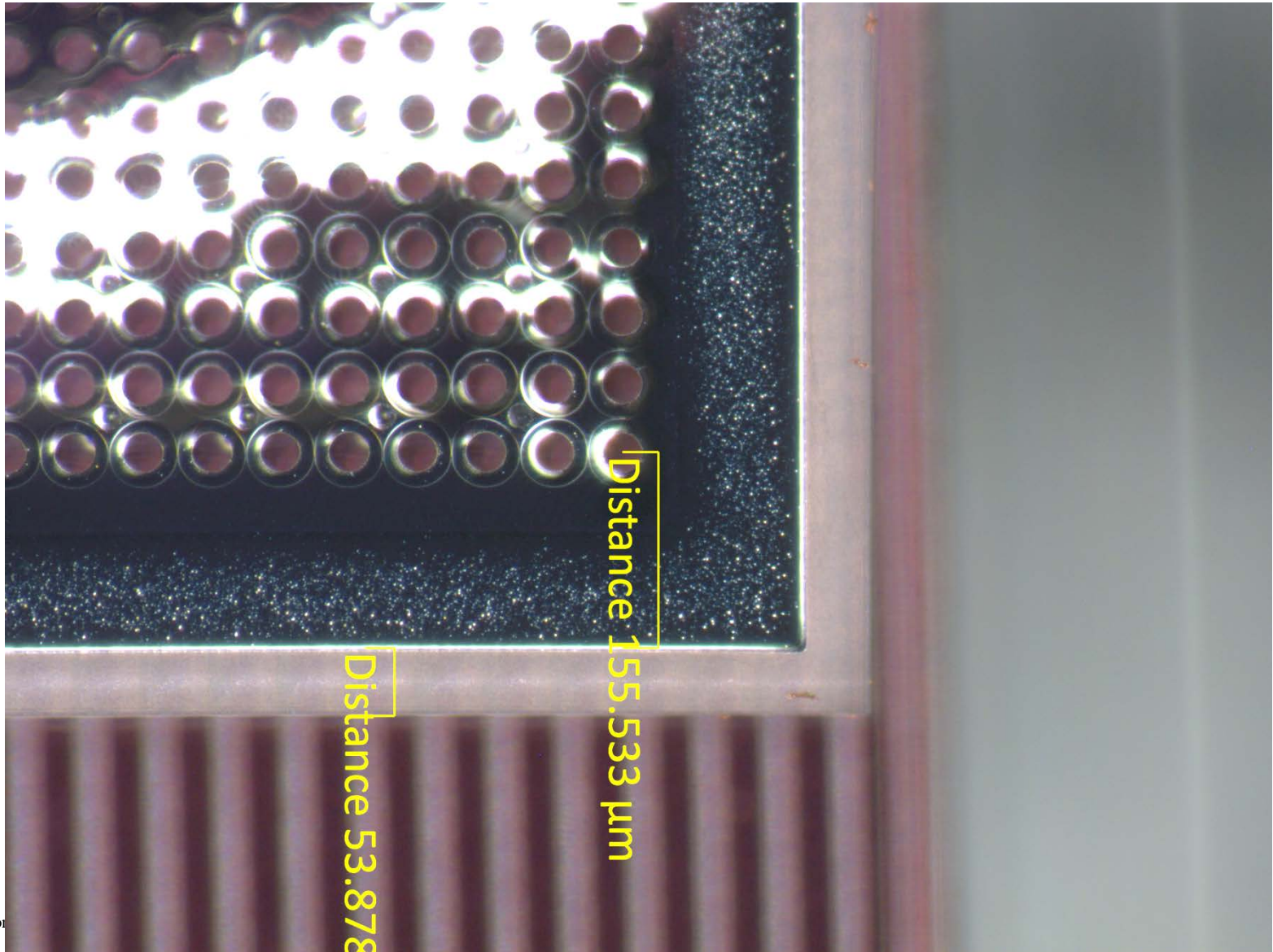
**All under discussion**

Nikhef/Bonn LepCol meeting  
Sept 26, 2016

# Bondpad damage: possible short

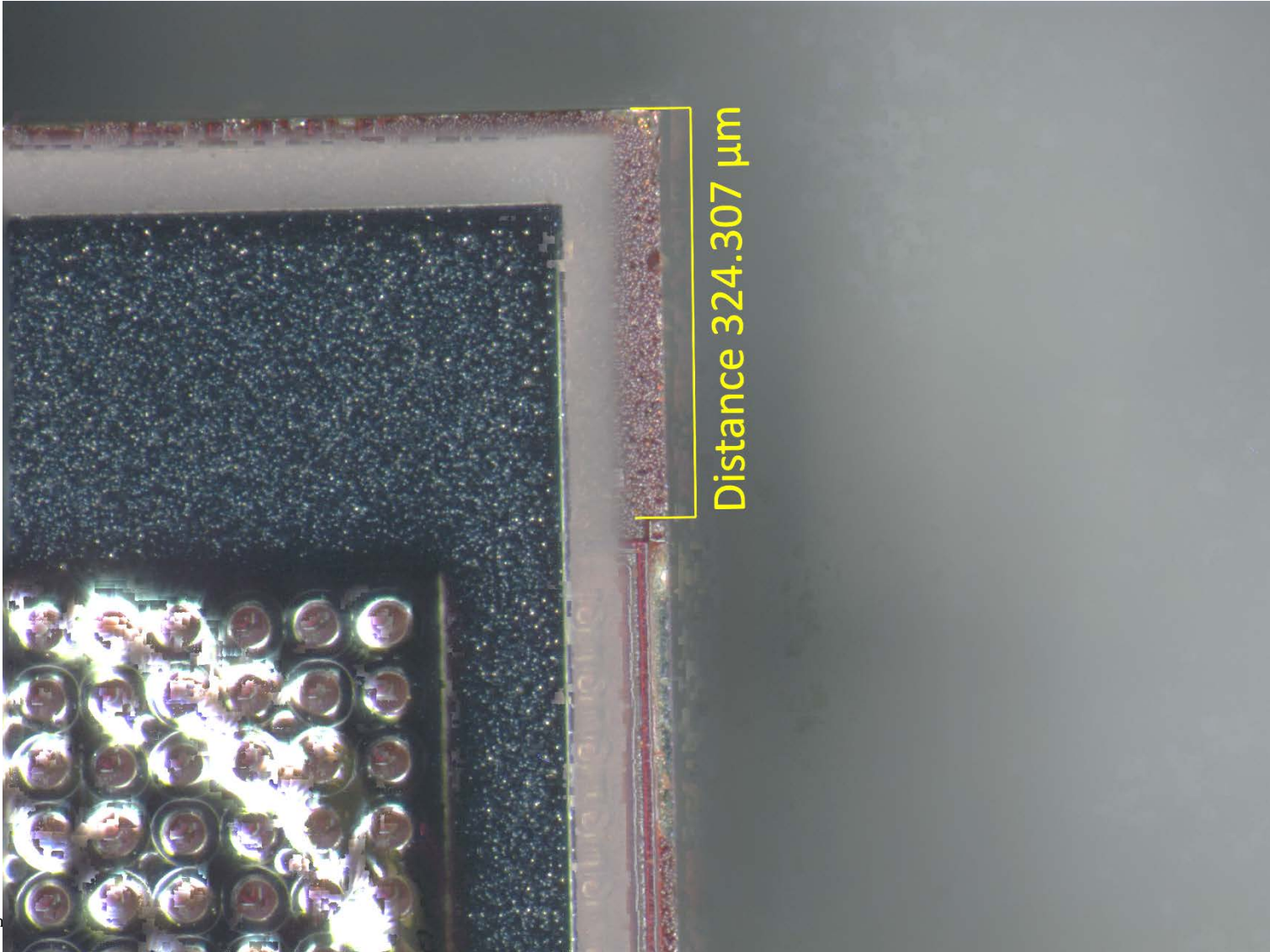


# Hard to add a Vgrid connection on this point



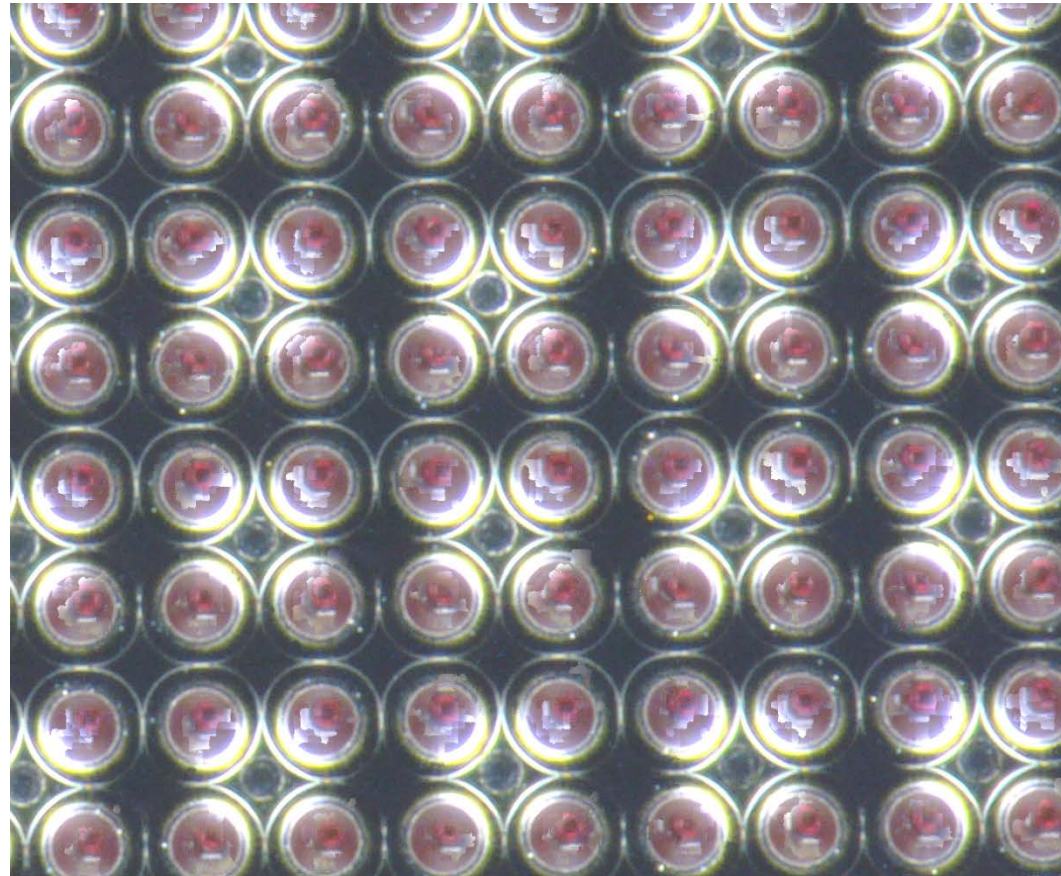


# Wide dyke opposite wire bonds where we don't need it



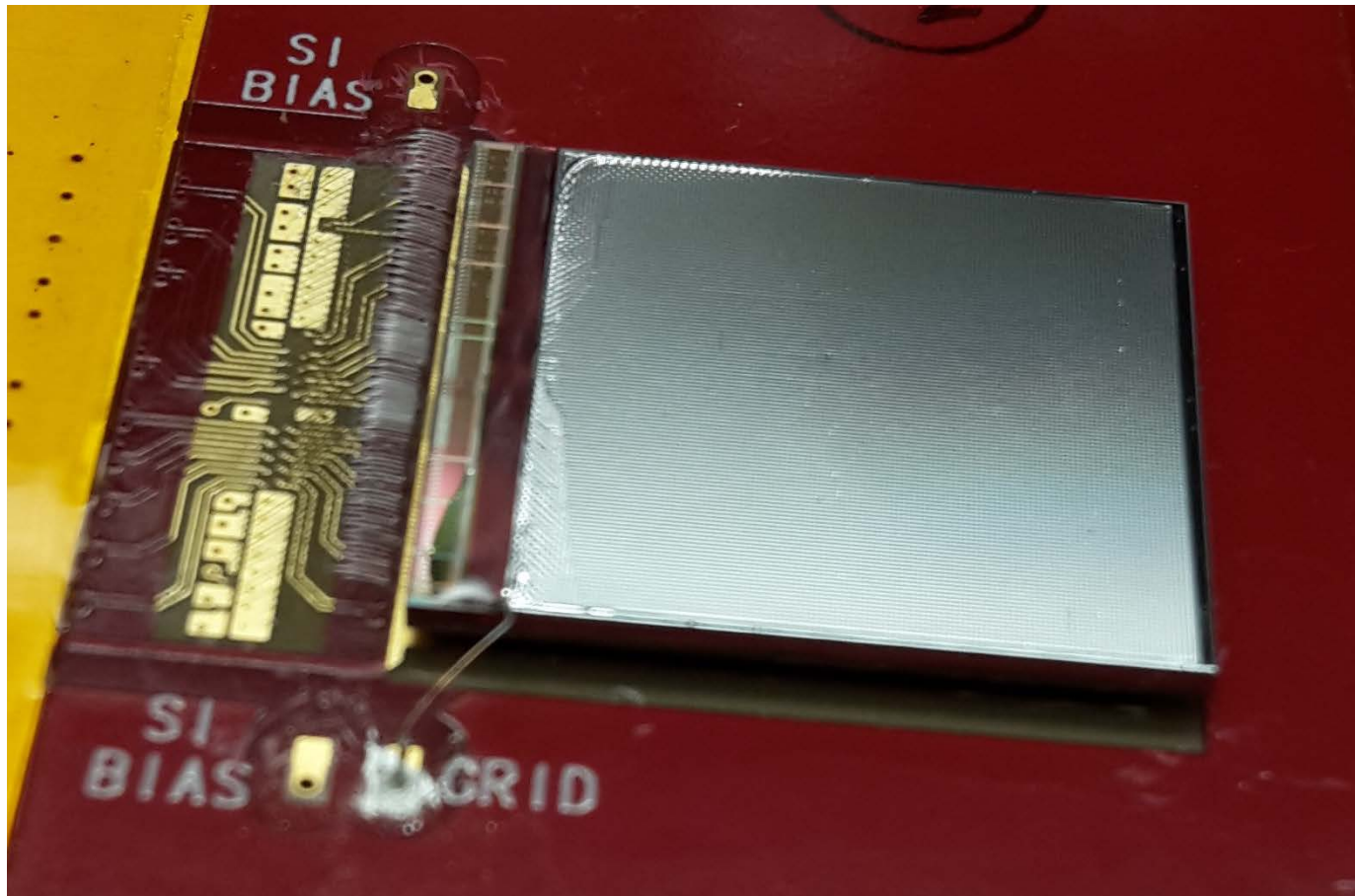
# Alignment grid to pixels

- Here  $\sim 10 \mu\text{m}$  error
- But different from previous slide
  - Also some scale factor involved
  - Not really important issue



# Single chip module

- Grid connected by 70 um Cu wire and conductive glue

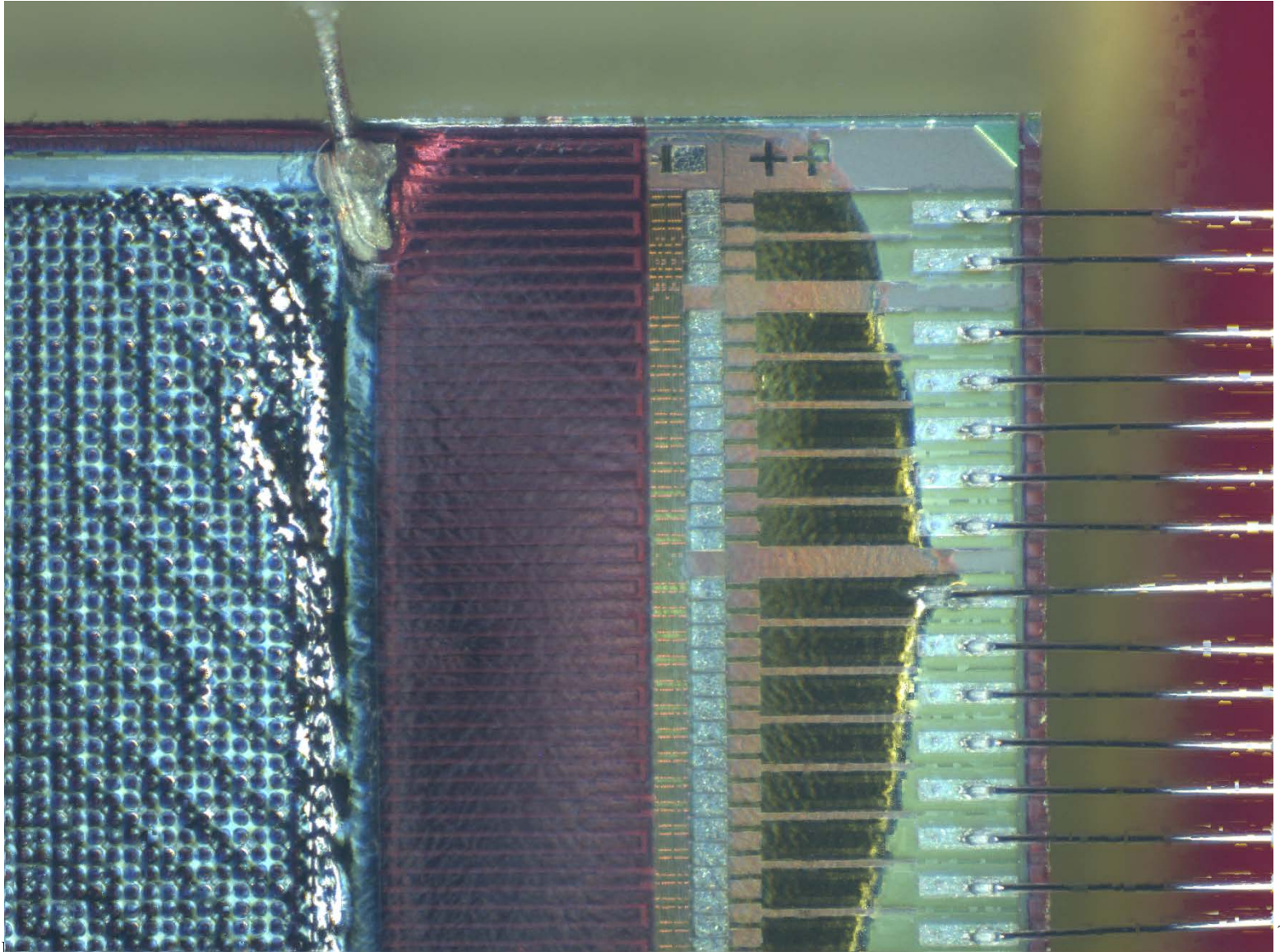


Fred Hartjes



# Grid connection

- Protected by GlopTop along full chip width



# Conclusions

- HV connection to grid not easy
  - Doable for few prototype chips
- We do need a new grid design with much wider dyke at wire bond side
  - => new masks
- Don't start with a new wafer using the existing masks



**SPARE**

- In progress/ under discussion
- Going from one chip to another on same carrier
  - 3 pixels sacrificed
- Going from one chip to another on neighbouring carrier
  - 4 pixels sacrificed
  - 28.6 => 28.435

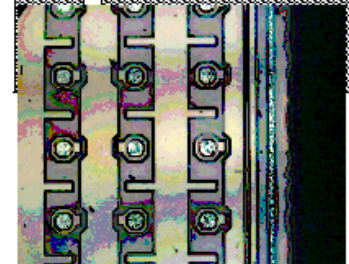
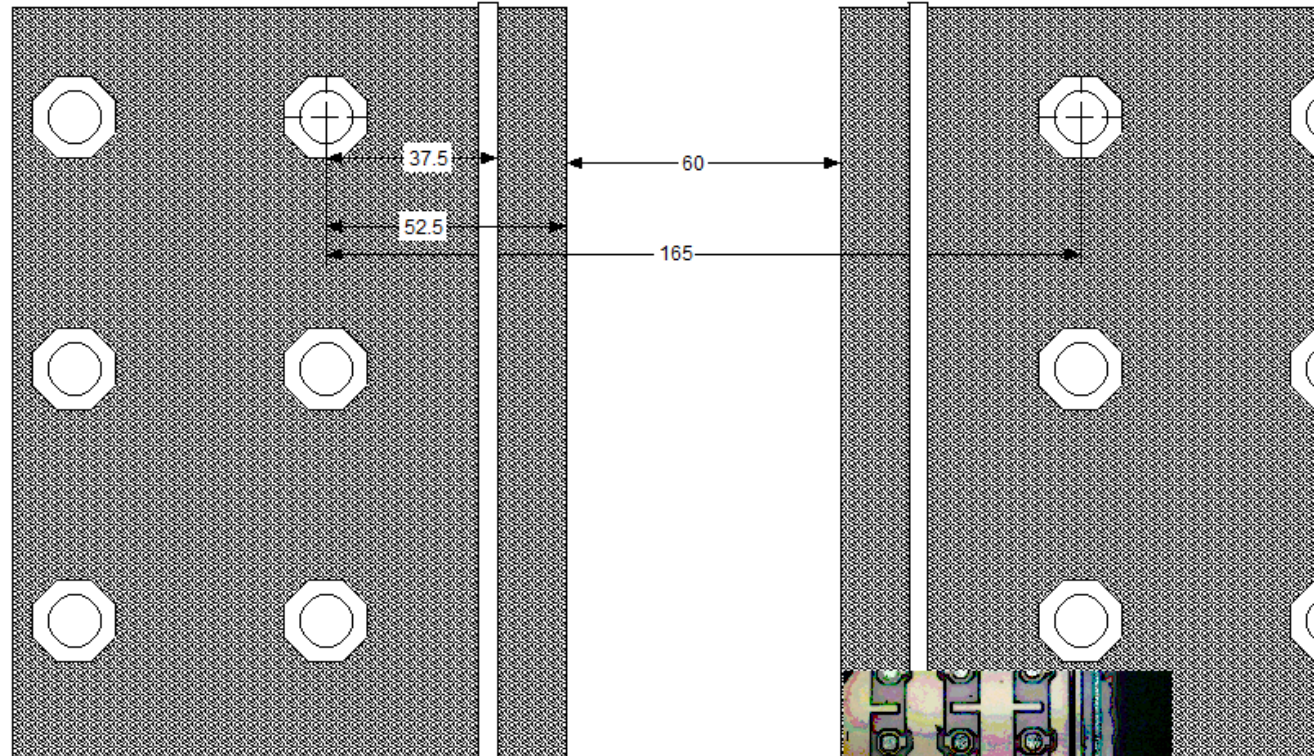
# List of parameters

**First approach, to be updated  
Put this on a Nikhef server with  
read access to everybody (incl Bonn)**

<b>Mechanical</b>									
Item	Values (um)			Angle (mrad)		Reference			remarks
	X	Y	Z	hor. Plane	vert. plane	X	Y	Z	
position InGrid of chips	± 20	± 20	± 20	1	1	PCB ref marks	PCB ref marks	foot T	
chip to chip distance		60							
last pixel Ch1 1st pixel CH2		165							
chip to chip distance mod 1 to mod 2		115							
last pixel mod1 to 1st pixel mod 2		220							
module to module pitch		28435							
position PCB ref marks	± 20	± 20	± 100	1	1	carrier edge	carrier edge	carrier foot	
Top guard electrode	± 50	± 50	500± 20	10	1	carrier edge	carrier edge	chip dyke	
chip edge to PBC			100						
chip dimension edge to edge			14130						
<b>Electrical</b>									
	Value								
Grid potential Vgrid (V)	~-400± 4								
Grid supply resistor (Ω)	100M								each chip
drift field E (V/cm)	-100								
Guard potential (V)	Vgrid + E*Zguard								
Guard supply resistor (Ω)	100M								

# Inter chip distance on same carrier

- Wafer cutting at IZM is very precise
- => We may position the chips very close to another
  - Going from one chip to another only **two** pixels are missing
  - => 165  $\mu\text{m}$  distance between centre last pixel to first pixel
  - 60  $\mu\text{m}$  edge to edge (nominal)



- Info from Martin van Beuzekom

## TP3 chip-chip distance

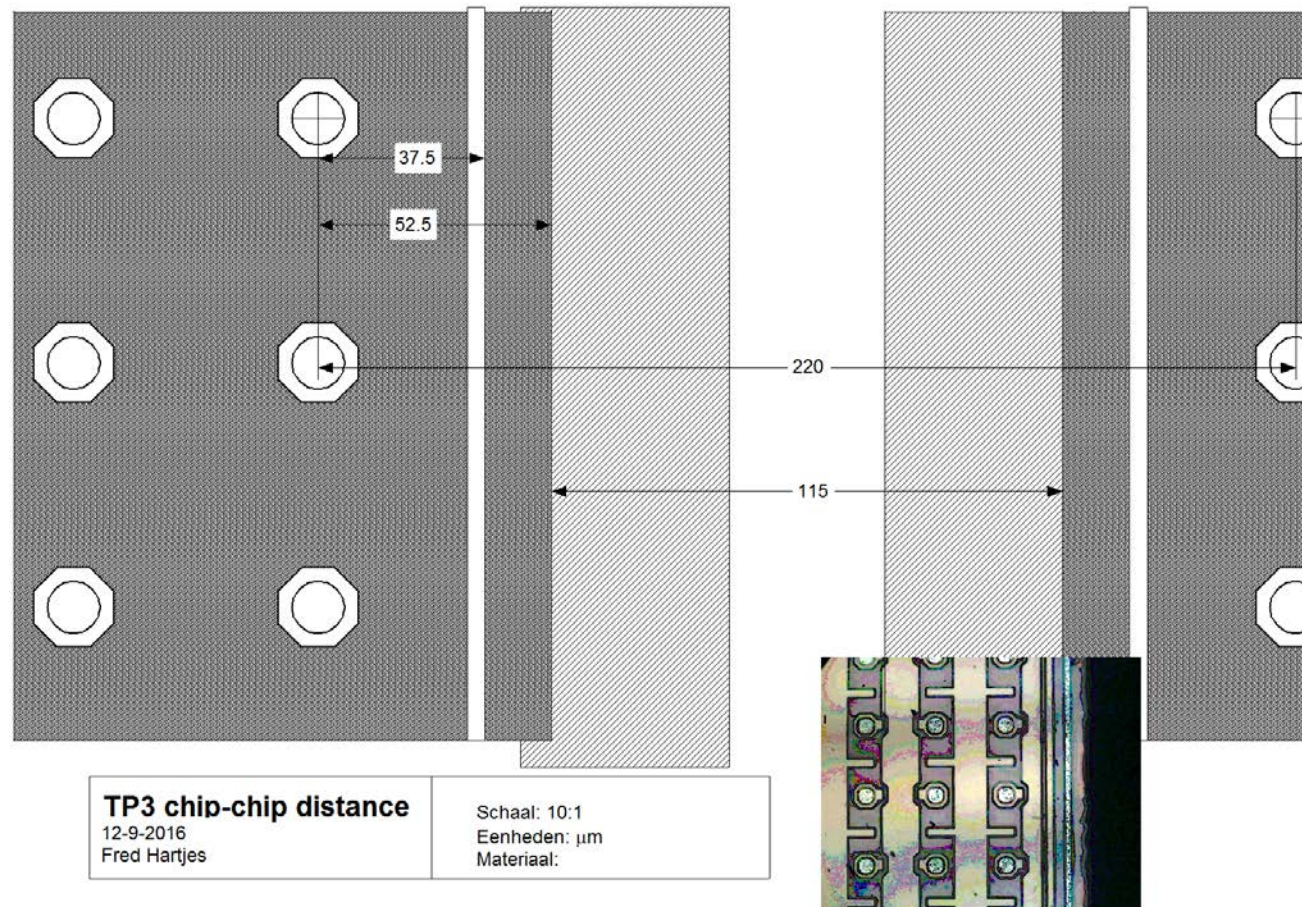
8-7-2016  
Fred Hartjes

Schaal: 10:1  
Eenheden: mm  
Materiaal:



# Inter chip distance to another carrier

- Going from one chip to another **three** pixels are sacrificed
- $\Rightarrow$  220  $\mu\text{m}$  distance between centre last pixel to first pixel
- 115  $\mu\text{m}$  edge to edge (nominal)



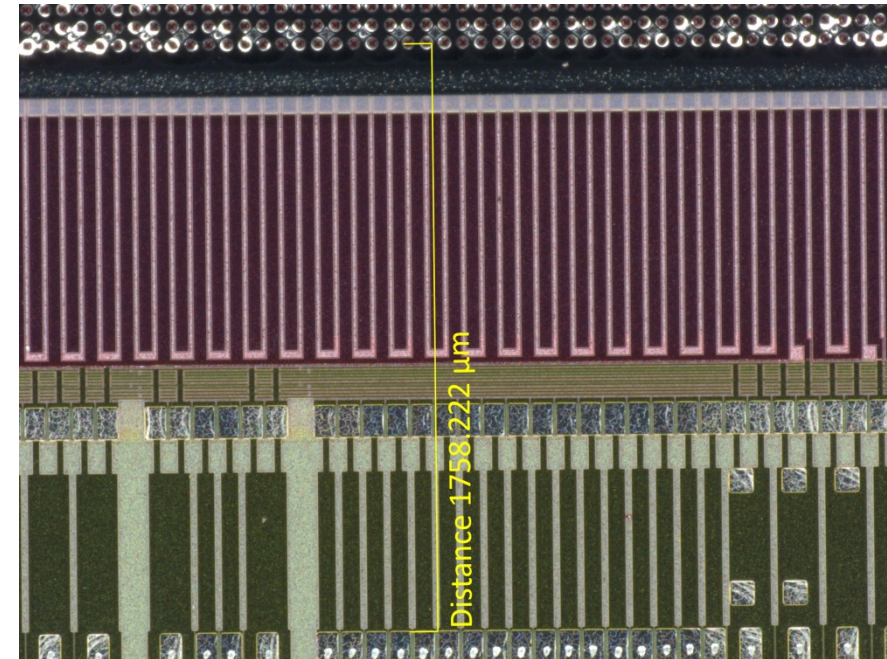
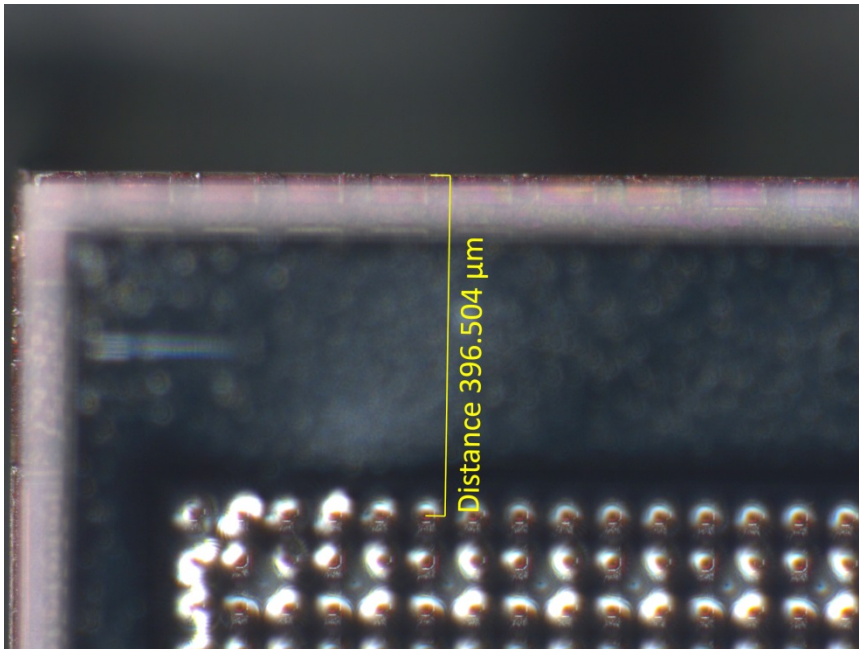
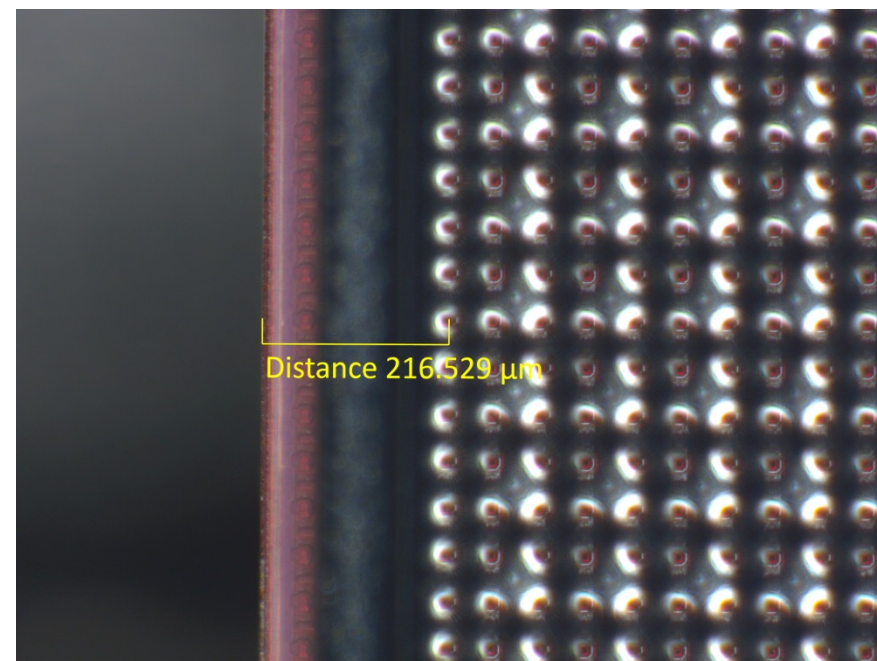
# Assembly / alignment method

- Mount PCB on carrier
  - Refer to two carrier edges using jig with reference marks
  - AND refer to reference marks on PCB
- Mount chips on carrier
  - 2 chips on one side simultaneously
  - XY: refer to grid hole pattern
    - rough alignment using bonding pads ( $N \times 55 \mu\text{m}$ )
  - AND refer to reference marks on PCB
  - Z: refer to grid (fixed height of alignment jig)
- Mount guard electrode
  - XY: refer edges to reference marks on PCB (tolerance  $100 \mu\text{m}$ )
  - Provide a 1 mm hole at the PCB reference marks
  - Z: let sides of the guard rest on dykes
    - Guard should fabricated bit hollow
- Module to module
  - XY: refer to PCB reference marks



- Sides
  - 3 pixels lost
- Top
  - 6 pixels lost
- Bottom
  - No pixels lost

# dykes





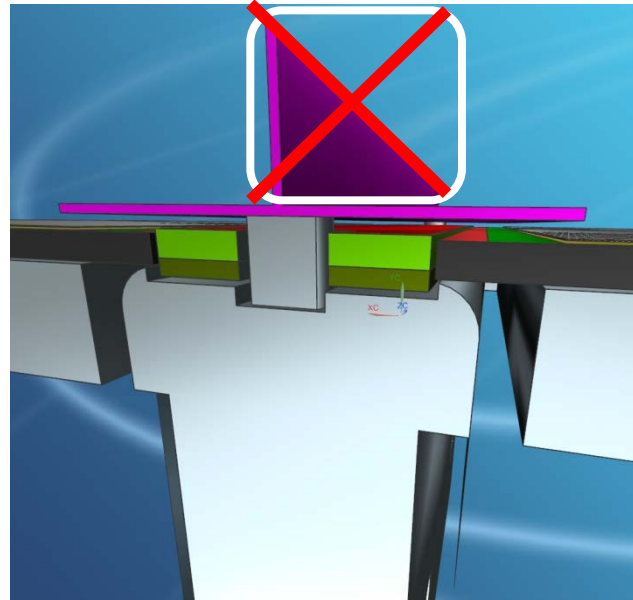
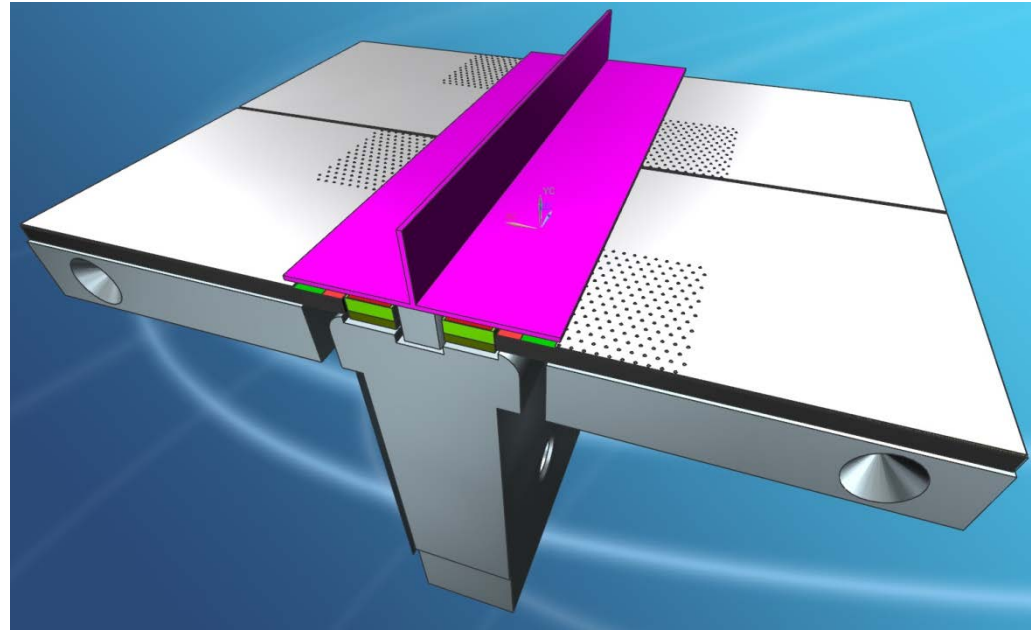
# Dyke widths

- Presently
  - $256 \times 256 = 65536$  pixels available
  - $250 \times 250 = 62500$  (95.4%) used
- Alternative
  - Narrow top dyke to 3 pixels like side dykes
  - $\Rightarrow 63250$  (96,5%) used
  - Make bottom dyke (wire bond side) very wide  $\sim 1$  mm without obscuring pixels

# Reference slides

# LepCol Quad type C

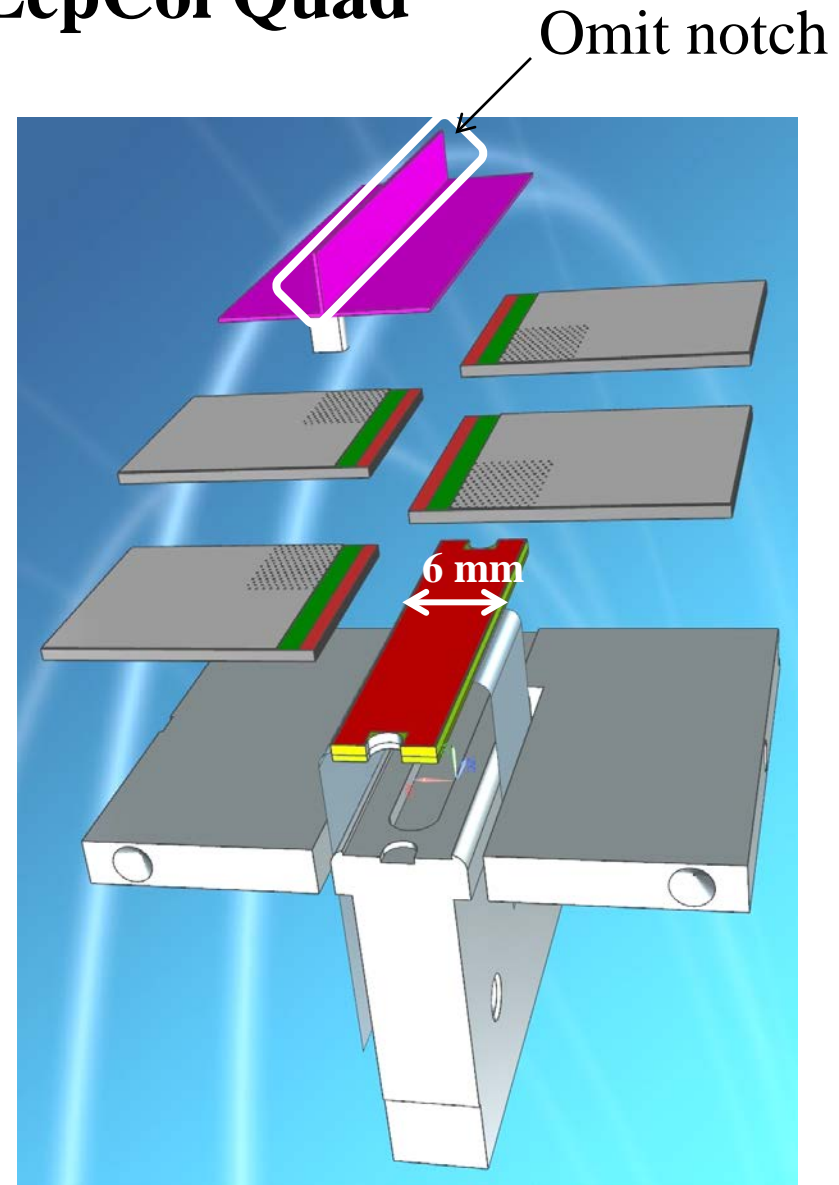
- **Being discussed, design will be adapted**
- **Using 4 TPX3 chips**
  - Glued on carrier
- Grouped around a central PCB for controls, signals and power lines
- Mounted on carrier structure (Aluminium => carbon based material)
- **Active surface ~70%**
- Cooling by common ground plate





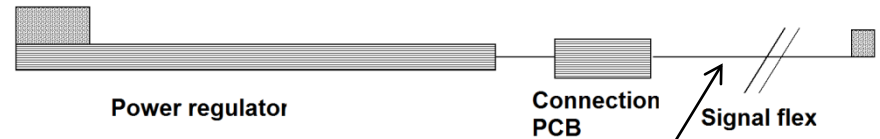
# Basic elements of LepCol Quad

- 1) 4 TPX3 chips + Ingrid
- 2) Connection PCB
  - 6 mm wide
  - Flex for
    - Power regulator LV + HV (grid + guard)
    - Signal/ control lines
  - Flexes loaded from aside
  - Slits may be very narrow ( $< 1$  mm)
- 3) Carrier block
  - Initially aluminium
  - To be fabricated in house or by spark erosion
  - Final carbon based material
    - Low mass
    - High thermal conductivity
- 4) Guard electrode
  - Thin ceramic metalized plate
  - Third support point will be added

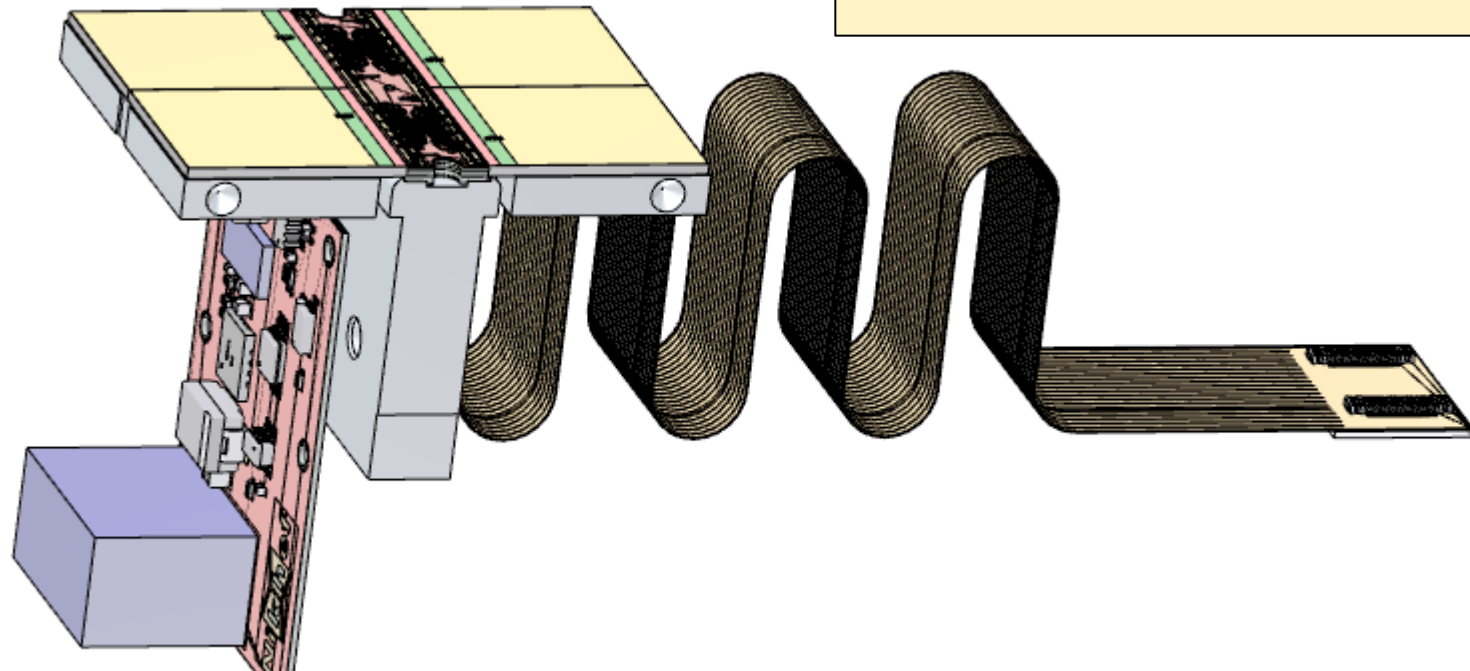


- Power regulation close to chips (< 2 cm)
  - Stabilising supply voltage from ~2.5 to 1.5 V
- Central PCB + signal flex + power board in one piece
  - No connectors between these elements
- ~20 W on power has to be cooled via carrier block
  - Max 40 W for extreme occupancy

# Electronics

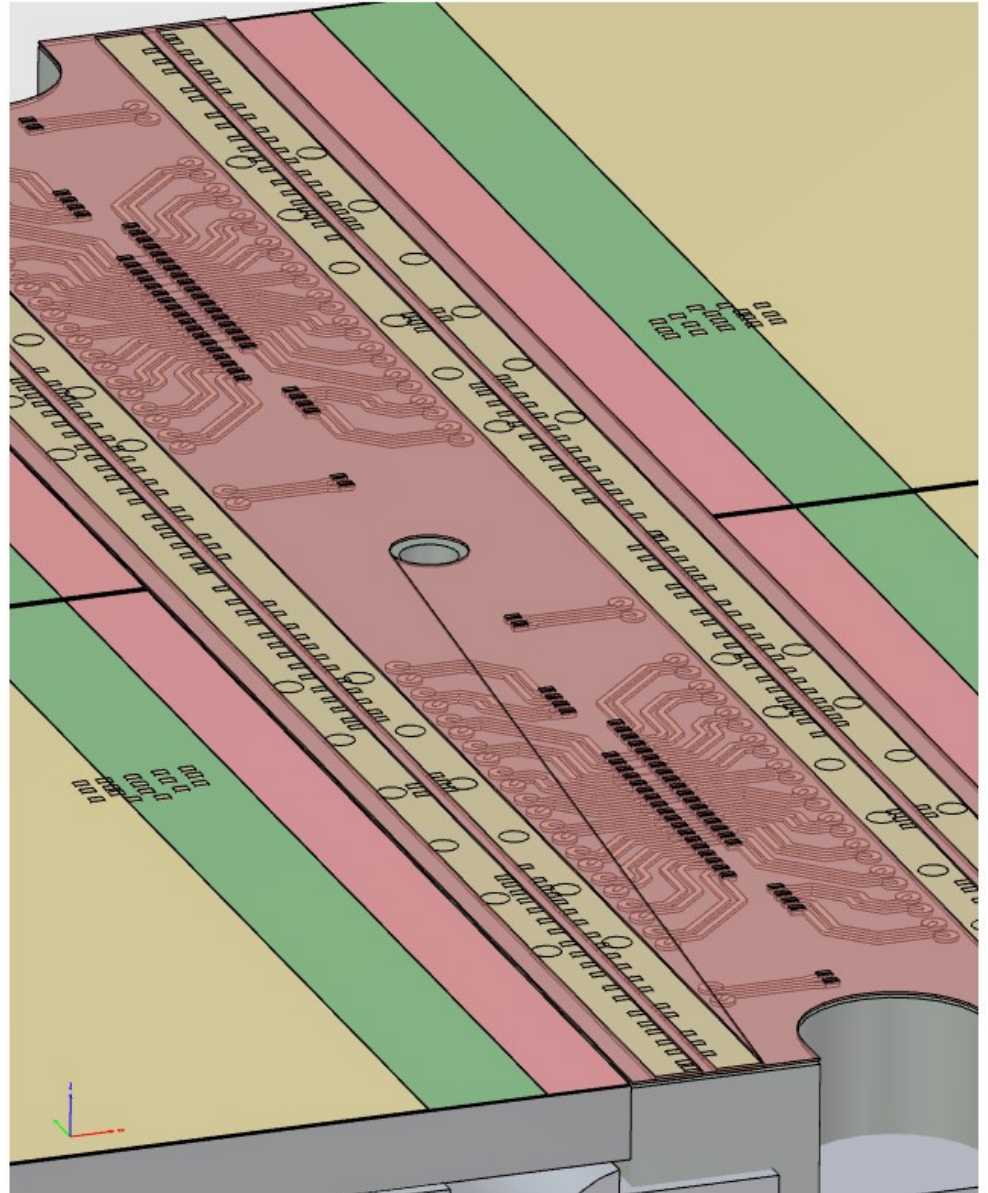


Flex with control and output signals may be long (up to 20 cm)

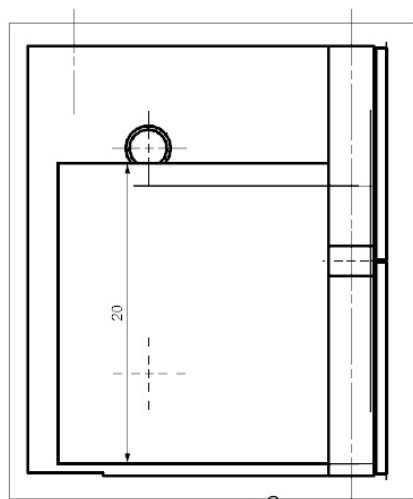


# PCB with traces

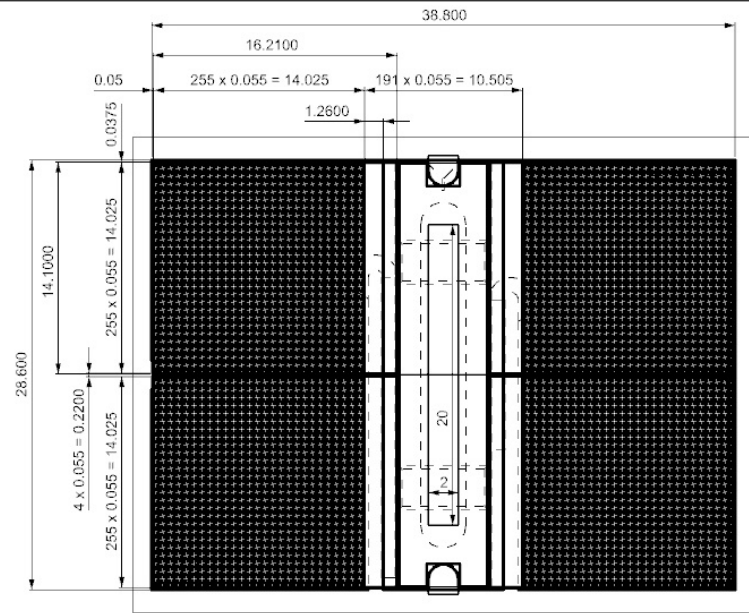
- 19 metal layers
- Additional hole in centre for guard support



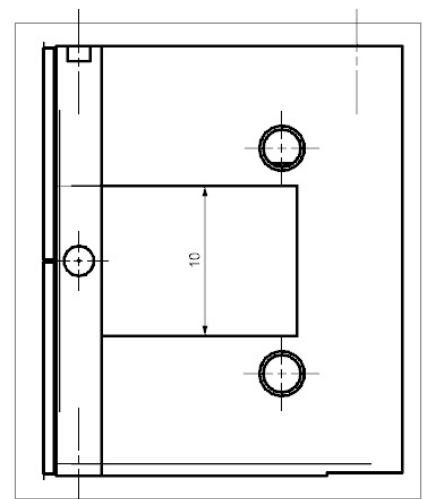
freu rnarjes



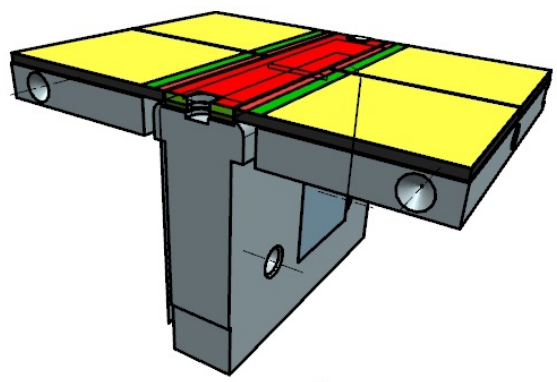
VIEW G  
SCALE 5:1



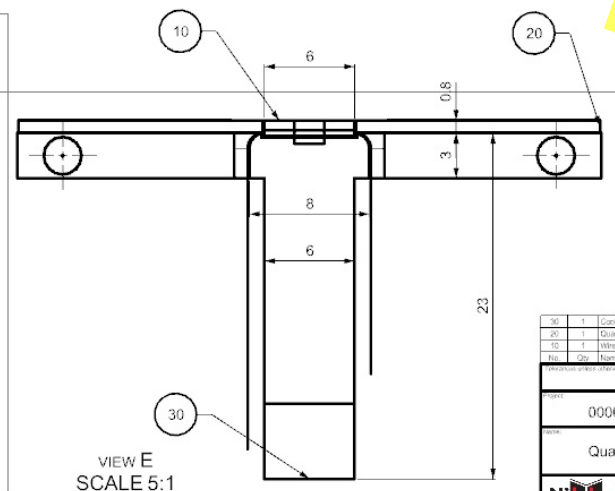
VIEW C  
SCALE 5:1



**38.8 x 28.6 mm**



VIEW F  
SCALE 4:1



VIEW E  
SCALE 5:1

10	1	Case in Block C (TimePh3) QUAD	05057A		
20	1	Quad TPX-3 Type B Assy	050710A		
10	1	Wire Bonding Board Type 3	050720A		
Rev	Qty	Name	Rev/Rev	Supplier name	Supplier code
000000-ILC / LepCol		Rev	1	28-Aug-2010	Rev/Rev
Quad TPX-3 Type C Main Assy		Rev	1-1	Revised	A
		Component number	05081-A	Revision	A
National Institute for Subatomic Physics Science, Technology, Innovation and Education		Part number	006081		